ASSP

1.0 GHz band Low Power I/Q Modulator For Direct Conversion

MB54608L/MB54608B

■ DESCRIPTION

The MB54608L/B is an I/Q Modulator for direct conversion method, and is used for up to 1.0 GHz band digital cellular phones such as GSM, PDC and so on.

MB54608L consists of a frequency doubler, a Flip-flop type quadrature phase shifter, I/Q modulator and a mixer for frequency offset with a separate power supply.

Fujitsu's advanced Bipolar process has realized very low current operation(Icc = 16.5 mA @3 V).

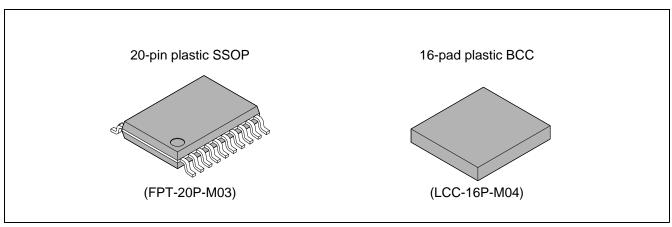
SSOP-20 and BCC-16 package are available.(MB54608L: SSOP-20, MB54608B: BCC-16)

■ FEATURES

- Supporting GSM frequency band
 Output frequency: 1.0 GHz (max.) Output power: -4 dBm(Typical, VBB = 1.0 Vp-p input)
- Low voltage operation: Vcc = 2.6 V to 3.8 V

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■ PACKAGES



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- Low current: Please refer to below table.
- Offset mixer on-chip: The separate power supply control is possible. (only MB54608L)
- Output power level switch (Mode) enables high power mode

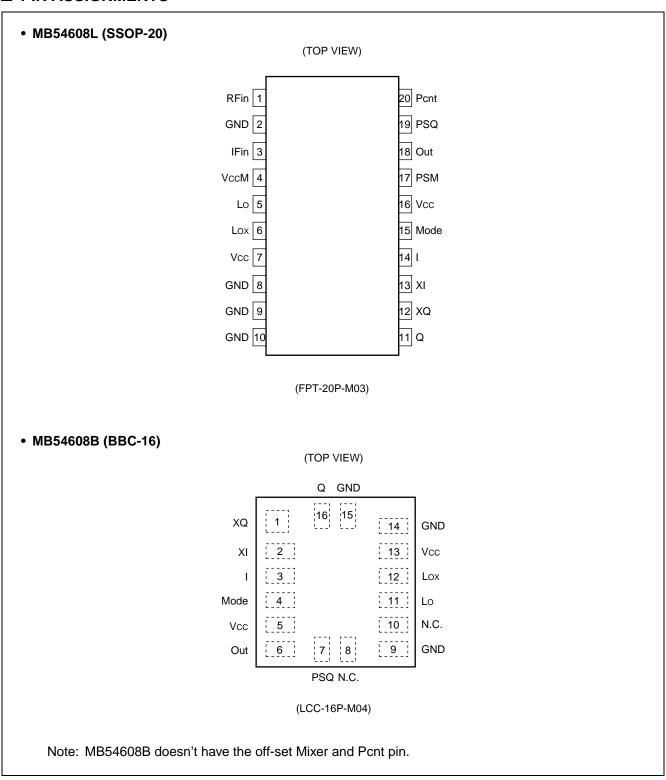
		Offset Mixe	er not used	Offset Mixer used		
		Mode = Open	Mode = GND	Mode = Open	Mode = GND	
Normal	Icc	16.5 mA	19.0 mA	22.5 mA	25.0 mA	
operation	Pout(V _{BB} =1.0 Vp-p)	−4 dBm	−2 dBm	−4 dBm	−2 dBm	
Power down	Ips	0.22 mA		0.44	· mA	

Note:Typical values

Further increase of the output power is possible by attaching a resistor at Pcnt pin.

• Operating temperature range: $Ta = -20 \text{ to } +75^{\circ}\text{C}$

■ PIN ASSIGNMENTS



■ PIN DESCRIPTIONS

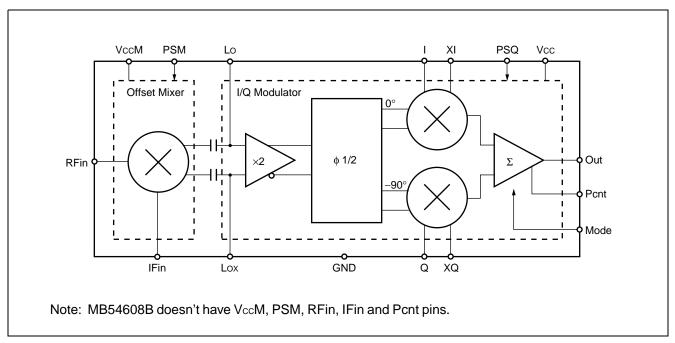
• MB54608L (SSOP-20)

Pin no.	Symbol	1/0	Descriptions				
1	RFin	ı	RF input for the offset mixer. When the offset mixer is not used, this pin should be opened.				
2	GND	—	Ground.				
3	IFin	I	IF input for the offset mixer. When the offset mixer is not used, this pin should be opened.				
4	VccM	_	Power supply for the offset mixer. Power-on/off is possible indepently to the modulator. When the offset mixer is not used, this pin should be switched OFF.				
5	Lo	I/O	Lo input for the I/Q modulator (Output for the offset mixer.)				
6	Lox	I/O	Lo complementary input for the I/Q modulator (Complementary output for the offset mixer.)				
7	Vcc	_	Power supply for the I/Q modulator.				
8	GND	_	Ground.				
9	GND	_	Ground.				
10	GND	_	Ground.				
11	Q	I	Q signal input for the I/Q modulator.				
12	XQ	I	Q signal complementary input for the I/Q modulator.				
13	XI	I	I signal complementary input for the I/Q modulator.				
14	I	I	I signal input for the I/Q modulator.				
15	Mode	_	Output mode switch. Mode = Open: Low power mode. Mode = GND: High power mode. This pin should be connected to ground or left open.				
16	Vcc	_	Power supply for the I/Q modulator.				
17	PSM	I	Power saving control for the offset mixer. When PSM = L(GND), power down mode is selected. When the offset mixer is not used, this pin should be connected to Vcc voltage level or ground.				
18	Out	0	Output for the I/Q modulator. (Open collector) Open is prohibited when power is supplied to Vcc pin.				
19	PSQ	I	Power saving control for the I/Q modulator. When PSQ = L(GND), power down mode is selected.				
20	Pcnt		Further, increasing the output power level is possible by attaching a resistor between Pcnt pin and ground externally.				

• MB54608B (BCC-16)

Pin no.	Pin nane	I/O	Descriptions
1	XQ	I	Q signal complementary input for the I/Q modulator.
2	XI	I	I signal complementary input for the I/Q modulator.
3	I	I	I signal input for the I/Q modulator.
4	Mode	_	Output mode switch. Mode=Open: Low power mode. Mode=GND: High power mode. This pin should be connected to ground or left open.
5	Vcc	_	Power supply for the I/Q modulator.
6	Out	0	Output for the I/Q modulator. (Open collector) Open is prohibited when power is supplied to Vcc pin.
7	PSQ	I	Power saving control for the I/Q modulator. When PSQ = L(GND), power down mode is selected.
8	N.C.	_	No connection.
9	GND	_	Ground.
10	N.C.	_	No connection.
11	Lo	I/O	Lo input for the I/Q modulator (Output for the offset mixer.)
12	Lox	I/O	Lo complementary input for the I/Q modulator (Complementary output for the offset mixer.)
13	Vcc	_	Power supply for the I/Q modulator.
14	GND	_	Ground.
15	GND	_	Ground.
16	Q	I	Q signal input for the I/Q modulator.

■ BLOCK DIAGRAM



■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rat	ting	Unit	Remarks	
Parameter	Symbol	Min.	Max.	Offic	Remarks	
Power supply voltage	Vcc	-0.5	+5.0	V		
Output voltage	Vo	-0.5	Vcc + 0.5 (<5.0)	V		
Input voltage	Vı	-0.5	Vcc + 0.5 (<5.0)	V		
Allowed voltage on the open collector pin	Voc	Vcc - 0.3 (-0.5)	Vcc + 0.3 (5.0)	V	Out pin, Open is prohibited.	
Output current	lo	0	+10	mA		
Storage temperature	Tstg	– 55	+125	°C		

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Cumbal		Value		Unit	Remarks
Parameter	Symbol	Min.	Тур.	Max.	Onit	Remarks
Power supply voltage	Vcc	2.6	3.0	3.8	V	
Input voltage	Vı	GND	_	Vcc	V	
Allowed voltage on the open collector pin	Voc	Vcc - 0.2	_	Vcc + 0.2	V	Out pin. Open is prohibited.
Operating temperature	Та	-20	_	+75	V	Ambient temperature.

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.

■ ELECTRICAL CHARACTERISTICS

1. DC CHARACTERISTICS (MB54608L, MB54608B)

 $(Ta = +25^{\circ}C, Vcc = 3.0 V)$

Parameter	Symbol		Value		Unit	Remarks		
raiailletei	Syllibol	Min.	Тур.	Max.	Ollit	i/ciliai n3		
					Offset mix.	Mode pin		
	_	12.0	16.5	24.5	mA	Not used	Open	_
Power supply current	Icc	13.5	19.0	28.0	mA	Not used	GND	DC. No AC
		16.0	22.5	33.5	mA	Used	Open	signal
		18.0	25.0	37.0	mA	Used	GND	input.
Power down current	IPS	_	220	310	μΑ	Not used	Don't	
Power down current		_	440	620	μΑ	Used	care	
Power down pin input voltage	VIHPS	Vcc × 0.7	_	_	V			
Fower down pin input voltage	VIL _{PS}	_	_	Vcc × 0.3	V			
	IIH _{PS}	_	_	5.0	μΑ	VIH = VCC		PSM,
Power down pin input current	IIL _{PS}	-50	_	_	μΑ	Vı∟ = GND		PSQ Value
Pcnt pin load resistance	Rcnt	50	_	_	Ω			

Note: MB54608B doesn't have Offset mix., so please refer to "offset mix. = Not used" column in regard to power supply current.

2. AC CHARACTERISTICS

• A case of the offset mixer is used. (only MB54608L)

 $(Ta = +25^{\circ}C, Vcc = 3.0 V)$

Parameter		Cumbal	Value			Unit	Remarks		
		Symbol	Min.	Тур.	Max.	Unit	Remarks		
	Operating band	fвв	DC	_	10	MHz			
Baseband	Input amplitude	V _{BB}	0.3	1.0	1.3	Vp-p	Single ended input		
input	Offset voltage	Vos	1.4	1.5	1.6	V	External offset voltage		
	Offset current	los		3.0	4.0	μΑ			
		f RF	_	1078.5	1100	MHz			
	Operating band	fıғ		130.5	500	MHz			
Offset Mixer		fLO	800	948	1000	MHz	Output		
	Input power level	P _{RF}	-15	-10	0	dBm			
		PıF	-15	-10	0	dBm			
	Operating band	fоит	800	948	1000	MHz			
RF output	SSB output	Роит	-8	-4	_	dBm	Mode pin is opened		
	power level	FOUL	-6	-2	_	dBm	Mode pin is grounded		
	Amplitude error	Aerr		2.0	3.0	%	RMS value	Vвв = 1.0 Vp-p	
Modulation accuracy	Phase error	Perr	_	1.5	2.0	deg.	RMS value	(single ended input)	
	Vector error	Verr		3.0	4.0	%	RMS value	f _{RF} = 1078.5 MHz	
Carrier suppression		CS	_	-35	-27	dBc	External offset. No offset adjustment.	PRF = -10 dBm fIF = 130.5 MHz PIF = -10 dBm fOUT = 948 MHz	
Image rejection		IR	_	-40	-28	dBc			
Adjucent cha	annel power	ACP	_	-65	-60	dB	$\Delta f = 50 \text{ kHz}$		
IF × 7 spurio	us	IF×7	_	-65	-60	dBc			

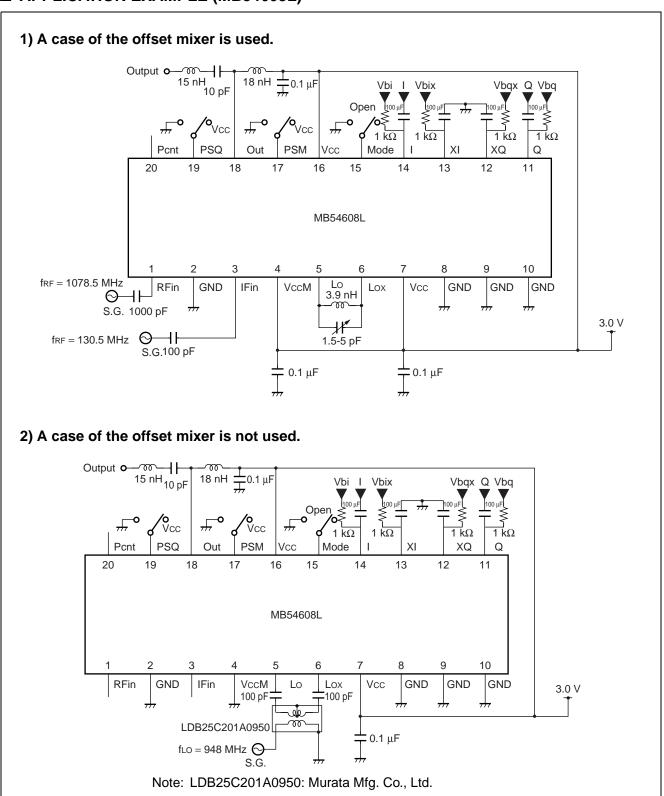
• A case of the offset mixer is not used. (MB54608L, MB54608B)

 $(Ta = +25^{\circ}C, Vcc = 3.0 V)$

Parameter		Symbol Value		Unit	Remarks			
		Symbol	Min.	Тур.	Max.	Ullit	Kemarks	
	Operating band	fвв	DC	_	10	MHz		
Baseband	Input amplitude	V _{BB}	0.3	1.0	1.3	Vp-p	Single ended	input
input	Offset voltage	Vos	1.4	1.5	1.6	V	External offse	t voltage
	Offset current	los	_	3.0	4.0	μΑ		
Lo input	Operating band	fLO	800	948	1000	MHz	Differential inp	out with balun.
Lo iriput	Input power	PLO	-15	-10	0	dBm		
	Operating band	fоит	800	948	1000	MHz		
RF output	SSB output	Роит	-8	-4	_	dBm	Mode pin is opened	
	power level	r level	-6	-2	_	dBm	Mode pin is grounded	
	Amplitude error	Aerr	_	2.0	3.0	%	RMS value	V _{BB} = 1.0 Vp-p
Modulation accuracy	Phase error	Perr	_	1.5	2.0	deg.	RMS value	(single ended input)
Vector error		Verr	_	3.0	4.0	%	RMS value	fLO = 948 MHz PLO = -10 dBm
Carrier suppression		CS	_	-35	-27	dBc	External offset. No offset ajustment.	(Differential input with balun).
Image rejection		IR	_	-40	-28	dBc		
Adjucent cha	annel power	ACP		-65	-60	dB	$\Delta f = 50 \text{ kHz}$	

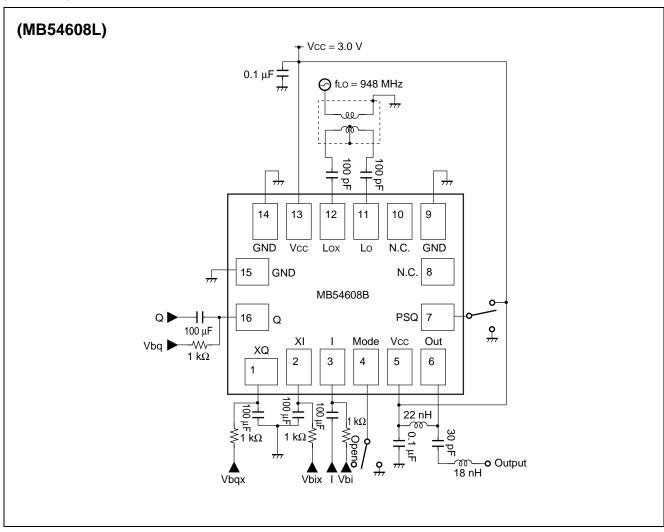
Notes: • Spec. of MB54608B is identical with MB54608L.
• When the offset mixer is not used, using a differential balun is recommended for input. (When the balun is not used, the changing carrier suppression may happen depending on the timing of powering up.)

■ APPLICATION EXAMPLE (MB54608L)



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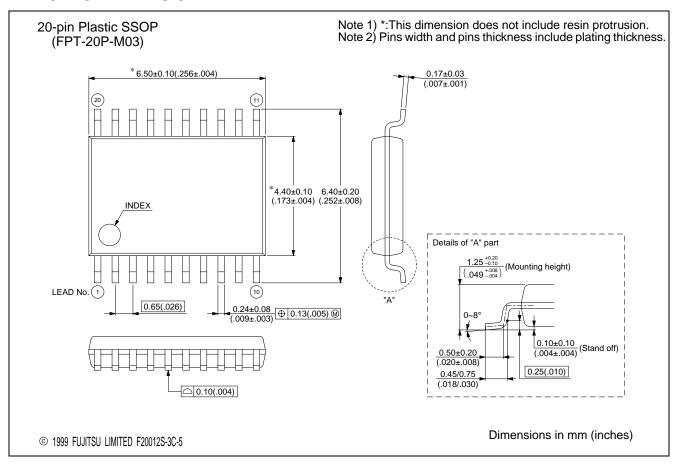
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■ ORDERING INFORMATION

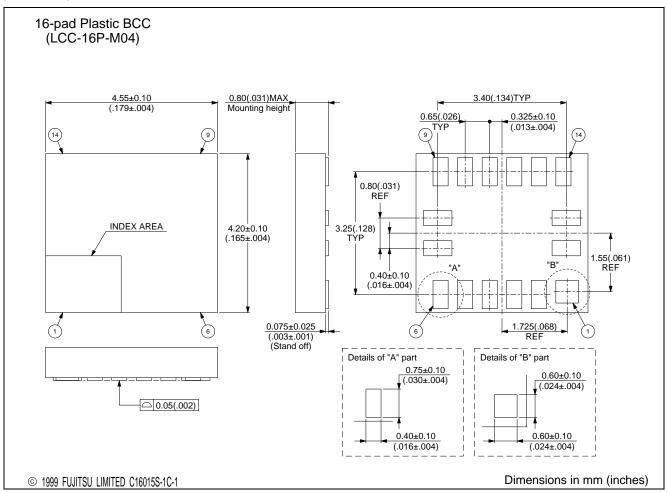
Part number	Package	Remarks
MB54608L PFV	20-pin, Plastic SSOP (FPT-20P-M03)	MB54608L
MB54608L PV1	16-pad, Plastic BCC (LCC-16P-M04)	MB54608B

■ PACKAGE DIMENSION



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